XN06542 (XN6542)

Silicon NPN epitaxial planer transistor

For high frequency amplification, oscillation, and mixing (Tr1), For medium-frequency amplification (Tr2)

Features

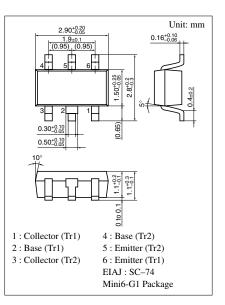
- Two elements incorporated into one package.
- Reduction of the mounting area and assembly cost by one half.

Basic Part Number of Element

• 2SC2480 + 2SC4444

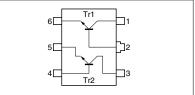
Parameter		Symbol	Ratings	Unit	
Tr1	Collector to base voltage	V _{CBO}	30	V	
	Collector to emitter voltage	V _{CEO}	20	V	
	Emitter to base voltage	V _{EBO}	3	V	
	Collector current	I _C	50	mA	
Tr2	Collector to base voltage	V _{CBO}	45	V	
	Collector to emitter voltage	V _{CEO}	35	V	
	Emitter to base voltage	V _{EBO}	4	V	
	Collector current	I _C	50	mA	
Overall	Total power dissipation	P _T	300	mW	
	Junction temperature	Tj	150	°C	
	Storage temperature	T _{stg}	-55 to +150	°C	

Absolute Maximum Ratings (Ta=25°C)



Marking Symbol: 5Z

Internal Connection



Note) The Part number in the Parenthesis shows conventional part number.

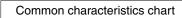
Electrical Characteristics (Ta=25°C)

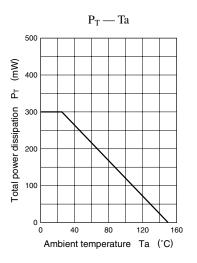
• Tr1

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V _{CBO}	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$	30			V
Emitter to base voltage	V _{EBO}	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$	3			v
Forward current transfer ratio	h _{FE}	$V_{CB} = 10V, I_E = -2mA$	25		250	
Base to emitter voltage	V _{BE}	$V_{CB} = 10V, I_E = -2mA$		720		mV
Common emitter reverse transfer capacitance	C _{re}	$V_{CB} = 10V, I_E = -1mA, f = 10.7MHz$		1.0	1.5	pF
Transition frequency	f _T	$V_{CB} = 10V, I_E = -15mA, f = 200MHz$	1000	1300	1600	MHz
Power gain	PG	$V_{CB} = 10V, I_E = -1mA, f = 100MHz$		20		dB
Reverse transfer capacitance	C _{rb}	$V_{CE} = 6V, I_C = 0, f = 1MHz$		0.8		pF

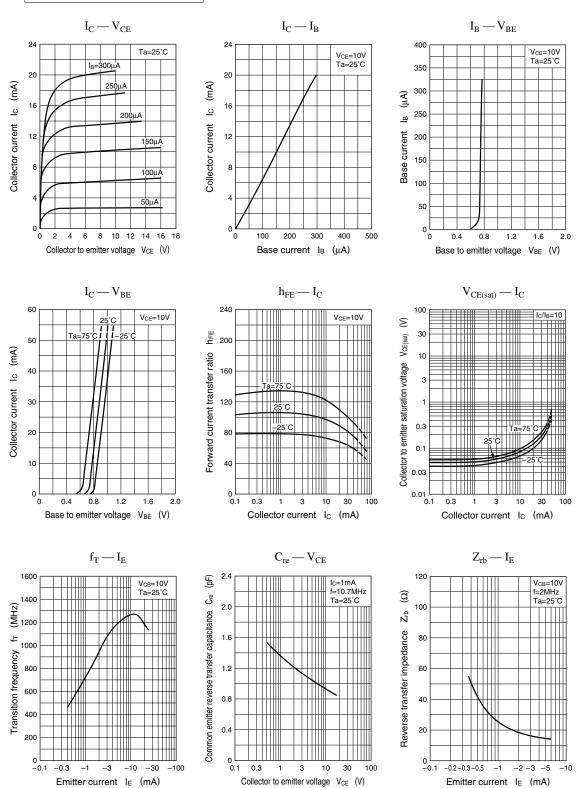
• Tr2

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V _{CBO}	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	45			V
Collector to emitter voltage	V _{CEO}	$I_{\rm C} = 1 {\rm mA}, {\rm IB} = 0$	35			v
Emitter to base voltage	V _{EBO}	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$	4			V
Collector cutoff current	I _{CEO}	$V_{CE} = 20V, I_B = 0$			10	μΑ
Forward current transfer ratio	h _{FE}	$V_{CB} = 10V, I_E = -10mA$	20	50	100	
Collector to emitter saturation voltage	V _{CE(sat)}	$I_C = 20 \text{mA}, I_B = 2 \text{mA}$			0.5	V
Transition frequency	f _T	$V_{CB} = 10V, I_E = -10mA, f = 100MHz$	300	500		MHz
Common emitter reverse transfer capacitance	C _{re}	$V_{CB} = 10V, I_E = -1mA, f = 10.7MHz$			1.5	pF
Power gain	PG	$V_{CB} = 10V, I_E = -10mA, f = 58MHz$		18		dB

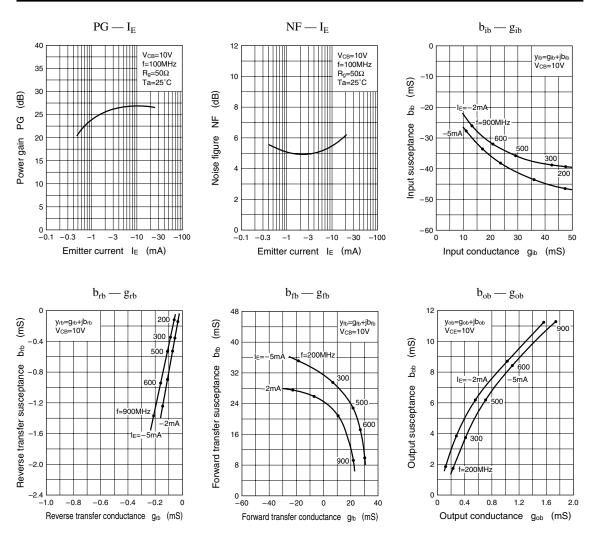




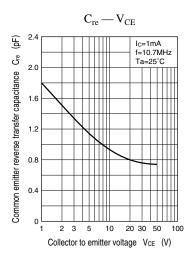
Characteristics charts of Tr1



Composite Transistors



Characteristics charts of Tr2 $I_C - V_{BE}$ $I_C - V_{CE}$ V_{CE(sat)} — I_C 80 60 100 $I_C/I_B=10$ V_{CE}=10V Ta=25°C S 70 I_B=2.0mA -25[!]C 30 Ta=75°C Collector to emitter saturation voltage V_{CE(sat}) 50 1.8mA (MA) Collector current lc (mA) 60 10 40 Collector current Ic 50 3 1.4mA 1.2mA 40 30 1.0mA 30 0.8mA 0.3 20 0.6mA 20 0.1 0.4mA 10 10 0.03 0.2mA 0 L 0 0.01 0.1 0 0 2 4 6 8 10 0.4 0.8 1.2 1.6 2.0 0.3 3 10 30 100 1 Collector to emitter voltage VCE (V) Base to emitter voltage V_{BE} (V) Collector current Ic (mA) $\mathbf{h}_{\mathrm{FE}} - \mathbf{I}_{\mathrm{C}}$ $f_T - I_E$ $C_{ob} - V_{CB}$ 120 600 3.0 V_{CE}=10V f=1MHz V_{CB}=10V (PF) I_E=0 Ta=25°C hFE Ta=25°C (MHz) 100 500 2.5 ပိ Forward current transfer ratio Collector output capacitance Transition frequency fr 400 80 2.0 Ta=75°C 300 60 25°C 1.5 25°C 200 40 1.0 20 100 0.5 0 L 0.1 0 0 0.3 1 3 10 30 100 -0.3 -1 -3 -10 -30 -100 2 3 5 10 20 30 50 100 Collector current Ic (mA) Emitter current IE (mA) Collector to base voltage V_{CB} (V)



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